

# AL - 402

The AL - 402 is a high - power GaAlAs IRED, with precision optical designed attachment lens. It emits parallel infrared lights.

## FEATURES

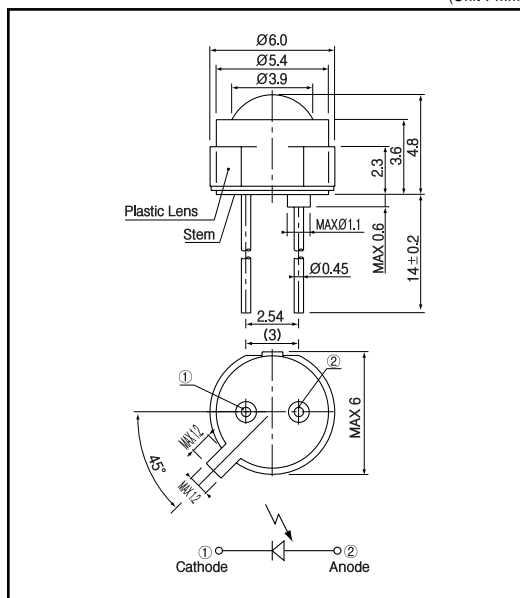
- Parallel rays
- Low profile
- sidelooking plastic package

## APPLICATIONS

- Encoders
- Emitters for automatic focusing

## DIMENSIONS

(Unit : mm)



## MAXIMUM RATINGS

(Ta=25 )

Item	Symbol	Rating	Unit
Reverse voltage	V <sub>R</sub>	5	V
Forward current	I <sub>F</sub>	100	mA
Pulse forward current	I <sub>FP</sub>	0.3	A
Power dissipation	P <sub>0</sub>	150	mW
Operating temp.	T <sub>opr.</sub>	- 25 ~ +70	
Storage temp.	T <sub>stg.</sub>	- 30 ~ +80	
Soldering temp. *1	T <sub>sol.</sub>	240	

\*1. For MAX.5 seconds at the position of 2 mm from the package

## ELECTRO-OPTICAL CHARACTERISTICS

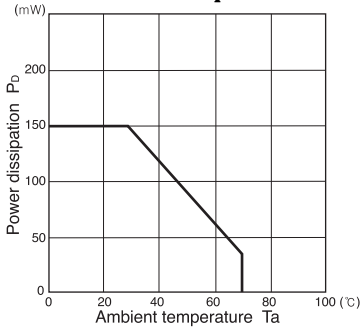
(Ta=25 )

Item	Symbol	Conditions	Min.	Typ.	Max.	Unit.
Forward voltage	V <sub>F</sub>	I <sub>F</sub> =50mA		1.4	2.0	V
Reverse current	I <sub>R</sub>	V <sub>R</sub> =5V			10	μA
Capacitance	C <sub>t</sub>	f=1MHz		20		pF
Radiant intensity	P <sub>0</sub>	I <sub>F</sub> =50mA		2.2		mW/sr
Peak emission wavelength	λ <sub>p</sub>	I <sub>F</sub> =50mA		910		nm
Spectral bandwidth 50%		I <sub>F</sub> =50mA		50		nm
Half angle					12	deg.
Effective emitting diameter	D			Ø3.9		mm

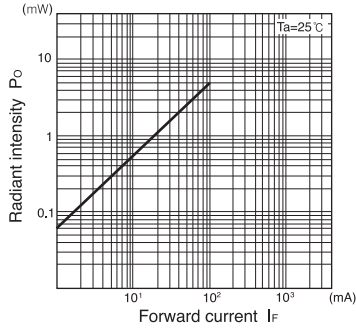
# Infrared Emitting Diodes(GaAlAs)

## AL - 402

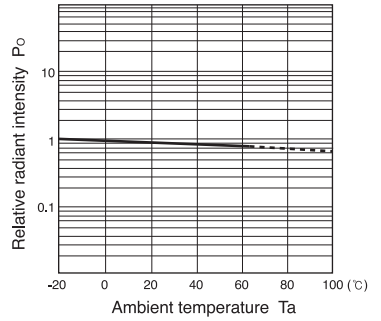
**Power dissipation Vs. Ambient temperature**



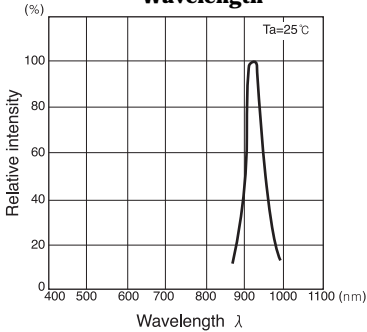
**Radiant intensity Vs. Forward current**



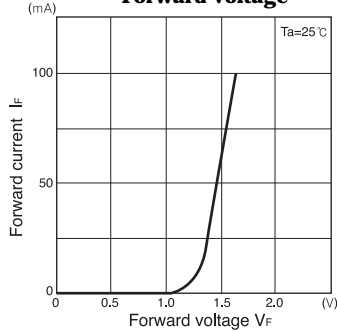
**Relative radiant intensity Vs. Ambient temperature**



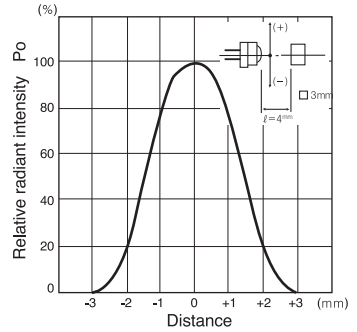
**Relative intensity Vs. Wavelength**



**Forward current Vs. Forward voltage**



**Radiant Pattern**



**Relative radiant intensity Vs. Distance**

